

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	ALL	MAX.	5	mA
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	10	mA
		-		15	
I_H	$I_T=100mA$		MAX.	5	mA
dV/dt	$V_D=540V$ Gate Open $T_j=110$		MIN.	20	V/ μs
(dV/dt) _c	(dI/dt) _c =1.8A/ms, $T_j=110$		MIN.	1	V/ μs

t_{on} $I_G=10mA$ y_3T_c -0.00404 224.52 535917.92 553.32 105.84 0.004 T_w 1.14 0 T_d [(0m)- T_d

ORDERING INFORMATION

J ST 136 W -800 T

FIG.1: Maximum power dissipation versus RMS on-state current

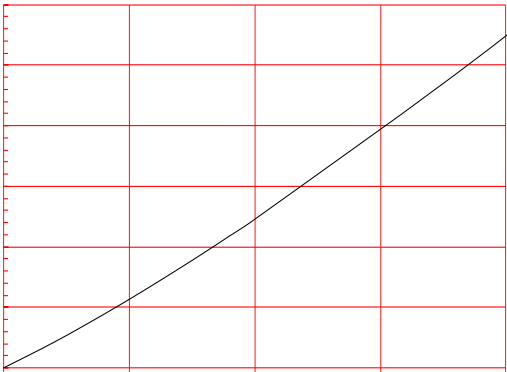
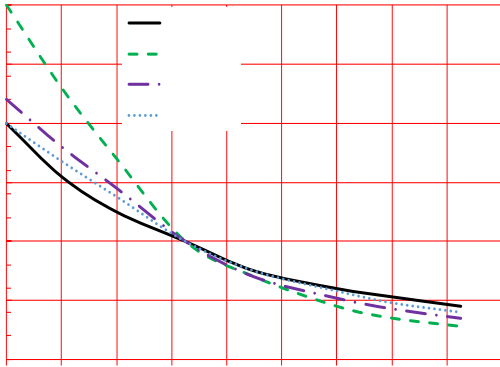


FIG.2: RMS on-state current versus case temperature

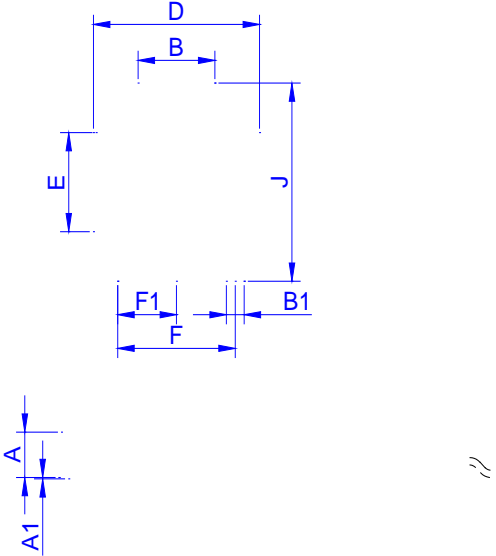
FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



JST136W-800T

JieJie M

PACKAGE MECHANICAL DATA



JST136W-800T

